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**Magneto-transport of filling controlled Mott insulator,  $\text{Sr}_2\text{IrO}_4$**

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[1] B. J. Kim et. al., PRL (2008).

[2] F. Wang and T. Senthil, PRL (2011).

[3] Y. Klein and I. Terasaki, J. Phys. : CM (2008).

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